# **CMOS MSI**

# Quad R-S Latches

The MC14043B and MC14044B quad R–S latches are constructed with MOS P–Channel and N–Channel enhancement mode devices in a single monolithic structure. Each latch has an independent Q output and set and reset inputs. The Q outputs are gated through three–state buffers having a common enable input. The outputs are enabled with a logical "1" or high on the enable input; a logical "0" or low disconnects the latch from the Q outputs, resulting in an open circuit at the Q outputs.

#### **Features**

- Double Diode Input Protection
- Three-State Outputs with Common Enable
- Outputs Capable of Driving Two Low-power TTL Loads or One Low-Power Schottky TTL Load Over the Rated Temperature Range
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

#### MAXIMUM RATINGS (Voltages Referenced to V<sub>SS</sub>)

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	DC Supply Voltage Range	-0.5 to +18.0	V
V <sub>in</sub> , V <sub>out</sub>	Input or Output Voltage Range (DC or Transient)	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>in</sub> , I <sub>out</sub>	Input or Output Current (DC or Transient) per Pin	±10	mA
P <sub>D</sub>	Power Dissipation, per Package (Note 1)	500	mW
T <sub>A</sub>	Ambient Temperature Range	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Temperature Derating: "D/DW" Packages: -7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.



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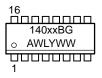
http://onsemi.com





SOIC-16 D SUFFIX CASE 751B SOEIAJ-16 F SUFFIX CASE 966

#### MARKING DIAGRAMS



SOIC-16



SOEIAJ-16

xx = Specific Device Code A = Assembly Location

 $\begin{array}{ll} \text{WL, L} &= \text{Wafer Lot} \\ \text{YY, Y} &= \text{Year} \\ \text{WW, W} &= \text{Work Week} \\ \text{G} &= \text{Pb-Free Indicator} \end{array}$ 

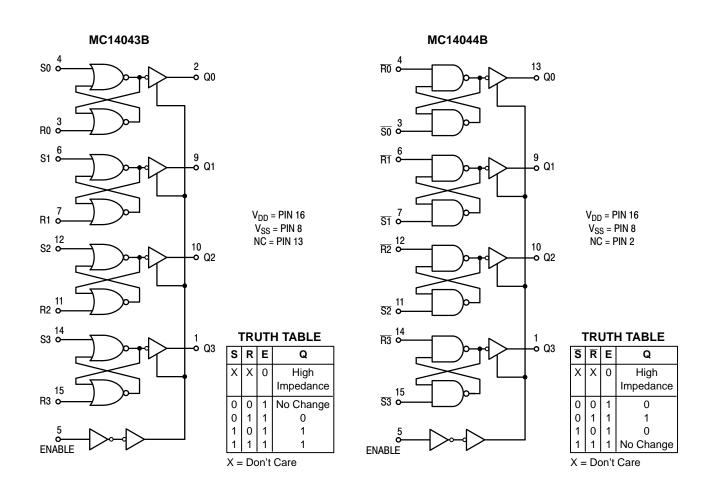
#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

### **PIN ASSIGNMENT**

_	MC14043	<u>BB</u>		MC1404	4B	_
Q3 [	1 • 1	16 ] V <sub>DD</sub>	Q3 [	1 ●	16	V <sub>DD</sub>
Q0 [	2 1	5 ] R3	NC [	2	15	] <del>S3</del>
R0 [	3 1	14 ] S3	S0 [	3	14	] <del>R3</del>
S0 [	4 1	3 D NC	R0 [	4	13	] Q0
Ε[	5 1	12 ] S2	E [	5	12	] <del>R</del> 2
S1 [	6 1	11 D R2	R1 [	6	11	] <del>S2</del>
R1 [	7 1	10 🛘 Q2	<u>S1</u> [	7	10	] Q2
V <sub>SS</sub> [	8	9 ] Q1	V <sub>SS</sub> [	8	9	] Q1

NC = NO CONNECTION



### **ELECTRICAL CHARACTERISTICS** (Voltages Referenced to V<sub>SS</sub>)

				- 5	5°C		25°C		125	5°C	
Characteristic		Symbol	V <sub>DD</sub> Vdc	Min	Max	Min	Typ (Note 2)	Max	Min	Max	Unit
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	"0" Level	V <sub>OL</sub>	5.0 10 15	- - -	0.05 0.05 0.05	- - -	0 0 0	0.05 0.05 0.05	- - -	0.05 0.05 0.05	Vdc
V <sub>in</sub> = 0 or V <sub>DD</sub>	"1" Level	V <sub>OH</sub>	5.0 10 15	4.95 9.95 14.95	- - -	4.95 9.95 14.95	5.0 10 15	- - -	4.95 9.95 14.95	- - -	Vdc
Input Voltage $(V_O = 4.5 \text{ or } 0.5 \text{ Vdc})$ $(V_O = 9.0 \text{ or } 1.0 \text{ Vdc})$ $(V_O = 13.5 \text{ or } 1.5 \text{ Vdc})$	"0" Level	V <sub>IL</sub>	5.0 10 15	- - -	1.5 3.0 4.0	- - -	2.25 4.50 6.75	1.5 3.0 4.0	- - -	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	V <sub>IH</sub>	5.0 10 15	3.5 7.0 11	- - -	3.5 7.0 11	2.75 5.50 8.25	- - -	3.5 7.0 11	- - -	Vdc
Output Drive Current (V <sub>OH</sub> = 2.5 Vdc) (V <sub>OH</sub> = 4.6 Vdc) (V <sub>OH</sub> = 9.5 Vdc) (V <sub>OH</sub> = 13.5 Vdc)	Source	I <sub>OH</sub>	5.0 5.0 10 15	-3.0 -0.64 -1.6 -4.2	- - -	-2.4 -0.51 -1.3 -3.4	-4.2 -0.88 -2.25 -8.8	- - -	-1.7 -0.36 -0.9 -2.4		mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	I <sub>OL</sub>	5.0 10 15	0.64 1.6 4.2	- - -	0.51 1.3 3.4	0.88 2.25 8.8	- - -	0.36 0.9 2.4	- - -	mAdc
Input Current		I <sub>in</sub>	15	_	±0.1	-	±0.00001	±0.1	_	±1.0	μAdc
Input Capacitance (V <sub>in</sub> = 0)		C <sub>in</sub>	ı	_	_	_	5.0	7.5	_	_	pF
Quiescent Current (Per Package)		I <sub>DD</sub>	5.0 10 15	- - -	1.0 2.0 4.0	- - -	0.002 0.004 0.006	1.0 2.0 4.0	- - -	30 60 120	μAdc
Total Supply Current (Note (Dynamic plus Quiesce Per Package) (C <sub>L</sub> = 50 pF on all output buffers switching)	nt,	I <sub>T</sub>	5.0 10 15			$I_{T} = (1$	.58 μΑ/kHz) .15 μΑ/kHz) .73 μΑ/kHz)	f + I <sub>DD</sub>			μAdc
Three–State Output Leaka Current	ge	I <sub>TL</sub>	15	-	±0.1	-	±0.0001	±0.1	_	±3.0	μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

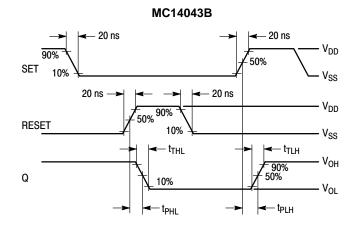
where:  $I_T$  is in  $\mu A$  (per package),  $C_L$  in pF,  $V = (V_{DD} - V_{SS})$  in volts, f in kHz is input frequency, and k = 0.004.

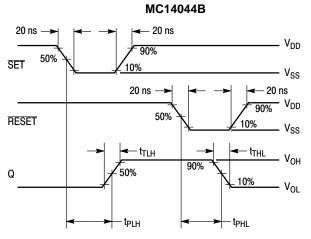
<sup>3.</sup> The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:

## **SWITCHING CHARACTERISTICS** (Note 5) ( $C_L = 50 \text{ pF}, T_A = 25^{\circ}\text{C}$ )

Characteristic	Symbol	V <sub>DD</sub> Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time $t_{TLH} = (1.35 \text{ ns/pF}) C_L + 32.5 \text{ ns}$ $t_{TLH} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{TLH} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$	t <sub>TLH</sub>	5.0 10 15	- - -	100 50 40	200 100 80	ns
Output Fall Time $t_{THL} = (1.35 \text{ ns/pF}) C_L + 32.5 \text{ ns}$ $t_{THL} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{THL} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$	t <sub>THL</sub>	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time $t_{PLH} = (0.90 \text{ ns/pF}) \text{ C}_{L} + 130 \text{ ns}$ $t_{PLH} = (0.36 \text{ ns/pF}) \text{ C}_{L} + 57 \text{ ns}$ $t_{PLH} = (0.26 \text{ ns/pF}) \text{ C}_{L} + 47 \text{ ns}$	t <sub>PLH</sub>	5.0 10 15	- - -	175 75 60	350 175 120	ns
$t_{PHL}$ = (0.90 ns/pF) $C_L$ + 130 ns $t_{PHL}$ = (0.90 ns/pF) $C_L$ + 57 ns $t_{PHL}$ = (0.26 ns/pF) $C_L$ + 47 ns	t <sub>PHL</sub>	5.0 10 15	- - -	175 75 60	350 175 120	ns
Set, Set Pulse Width	t <sub>W</sub>	5.0 10 15	200 100 70	80 40 30	- - -	ns
Reset, Reset Pulse Width	t <sub>W</sub>	5.0 10 15	200 100 70	80 40 30	- - -	ns
Three-State Enable/Disable Delay	t <sub>PLZ</sub> , t <sub>PHZ</sub> , t <sub>PZL</sub> , t <sub>PZH</sub>	5.0 10 15	- - -	150 80 55	300 160 110	ns

### **AC WAVEFORMS**



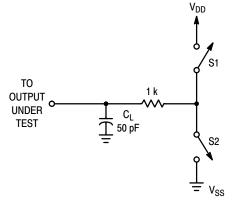


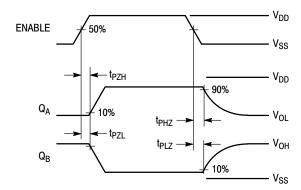
<sup>5.</sup> The formulas given are for the typical characteristics only at 25°C.
6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

### THREE-STATE ENABLE/DISABLE DELAYS

Set, Reset, Enable, and Switch Conditions for 3-State Tests

					MC14043B		B MC14044	
Test	Enable	S1	S2	Q	S	R	<u>s</u>	R
t <sub>PZH</sub>		Open	Closed	Α	$V_{DD}$	V <sub>SS</sub>	V <sub>SS</sub>	$V_{DD}$
t <sub>PZL</sub>		Closed	Open	В	V <sub>SS</sub>	$V_{DD}$	$V_{DD}$	V <sub>SS</sub>
t <sub>PHZ</sub>	~	Open	Closed	Α	$V_{DD}$	V <sub>SS</sub>	V <sub>SS</sub>	$V_{DD}$
t <sub>PLZ</sub>	~	Closed	Open	В	V <sub>SS</sub>	$V_{DD}$	V <sub>DD</sub>	V <sub>SS</sub>





## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC14043BDG	SOIC-16 (Pb-Free)	48 Units / Rail
NLV14043BDG*	SOIC-16 (Pb-Free)	48 Units / Rail
MC14043BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14043BDR2G*	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
MC14043BFELG	SOEIAJ-16 (Pb-Free)	2000 Units / Tape & Reel

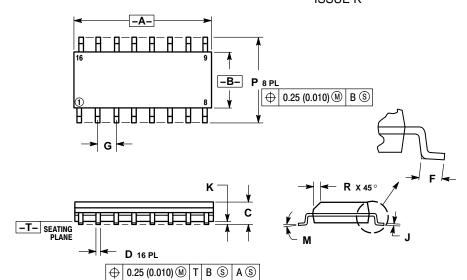
MC14044BDG	SOIC-16 (Pb-Free)	48 Units / Rail
NLV14044BDG*	SOIC-16 (Pb-Free)	48 Units / Rail
MC14044BDR2G	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel
NLV14044BDR2G*	SOIC-16 (Pb-Free)	2500 Units / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

### **PACKAGE DIMENSIONS**

#### SOIC-16 **D SUFFIX** CASE 751B-05 ISSUE K



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

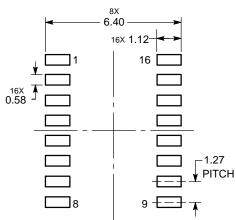
  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0 °	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

#### **SOLDERING FOOTPRINT\***

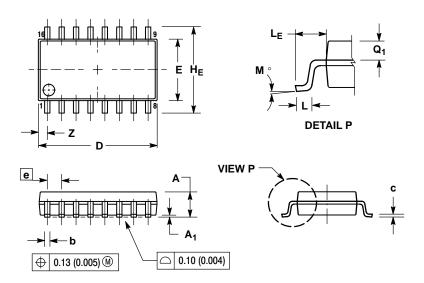


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

SOEIAJ-16 **F SUFFIX CASE 966 ISSUE A** 



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
- CONTROLLING DIMENSION: MILLIMETER.
- B. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (U.U.O) PER SIDE.

  TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.

  DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.10	0.20	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
$Q_1$	0.70	0.90	0.028	0.035
Z		0.78		0.031

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